

IRF634

N-channel mosfet transistor



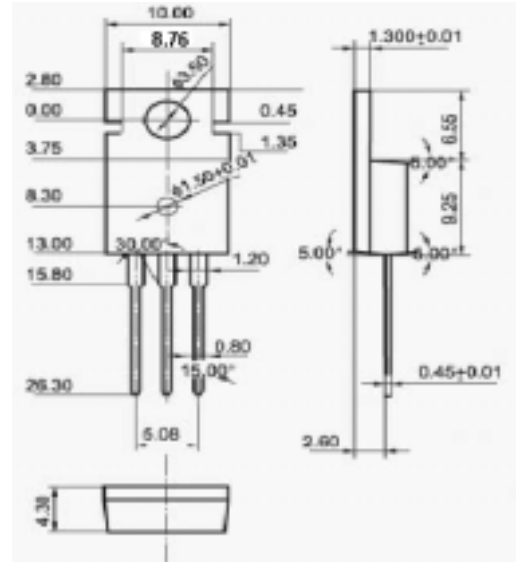
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◆ Features

- With TO-220 package
- Simple drive requirements
- Fast switching
- $V_{DSS}=250V$; $R_{DS(ON)} 0.45 \Omega$; $I_D=8.1A$
- 1.gate 2.drain 3.source

◆ Absolute Maximum Ratings $T_c=25$

| SYMBOL | PARAMETER | RATING | UNIT |
|-----------|-------------------------------------|----------|------|
| V_{DSS} | Drain-source voltage ($V_{GS}=0$) | 250 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| I_D | Drain Current-continuous@ $T_C=25$ | 8.1 | A |
| P_{tot} | Total Dissipation@ $T_C=25$ | 74 | W |
| T_j | Max. Operating Junction temperature | 150 | |
| T_{stg} | Storage temperature | -65~150 | |



TO-220

◆ Electrical Characteristics $T_c=25$

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|---------------|----------------------------------|---------------------------------|-----|-----------|------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS}=0$; $I_D=0.25mA$ | 250 | | V |
| $V_{GS(TH)}$ | Gate threshold voltage | $V_{DS}= V_{GS}$; $I_D=0.25mA$ | 2 | 4 | V |
| $R_{DS(ON)}$ | Drain-source on-stage resistance | $V_{GS}=10V$; $I_D=5.1A$ | | 450 | m |
| I_{GSS} | Gate source leakage current | $V_{GS}= \pm 20V$; $V_{DS}=0$ | | ± 100 | nA |
| I_{DSS} | Zero gate voltage drain current | $V_{DS}=250V$; $V_{GS}=0$ | | 25 | uA |
| V_{SD} | Diode forward voltage | $I_F=8.1A$; $V_{GS}=0$ | | 2.0 | V |